

EE 105 Discussion

Welcome!

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Today

- Exercise 1: S&S 2.93
- Exercise 2
- Exercise 3
- Exercise 4

S&S 2.93

D **2.93 Derive the transfer function of the circuit in Fig. P2.93 (for an ideal op amp) and show that it can be written in the form

$$\frac{V_o}{V_i} = \frac{-R_2/R_1}{[1 + (\omega_1/j\omega)][1 + j(\omega/\omega_2)]}$$

where $\omega_1 = 1/C_1 R_1$ and $\omega_2 = 1/C_2 R_2$. Assuming that the circuit is designed such that $\omega_2 \gg \omega_1$, find approximate expressions for the transfer function in the following frequency regions:

(a) $\omega \ll \omega_1$

(b) $\omega_1 \ll \omega \ll \omega_2$

(c) $\omega \gg \omega_2$

Use these approximations to sketch a Bode plot for the magnitude response. Observe that the circuit performs as an amplifier whose gain rolls off at the low-frequency end in the manner of a high-pass STC network, and at the high-frequency end in the manner of a low-pass STC network. Design the circuit to provide a gain of 40 dB in the “middle-frequency range,” a low-frequency 3-dB point at 200 Hz, a high-frequency 3-dB point at 200 kHz, and an input resistance (at $\omega \gg \omega_1$) of 2 k Ω .

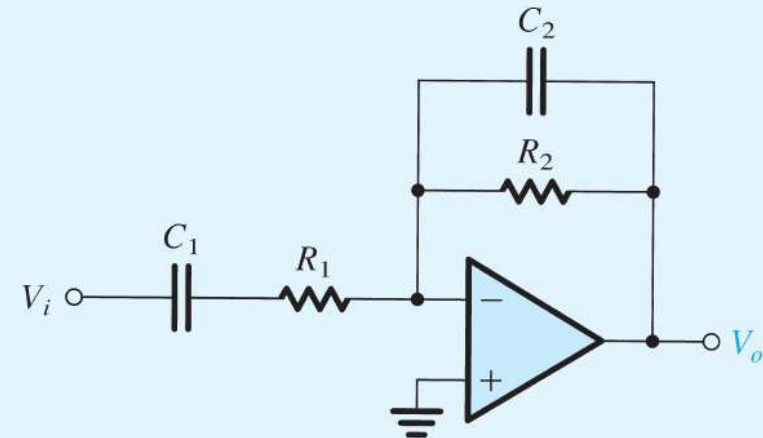


Figure P2.93

S&S 2.93

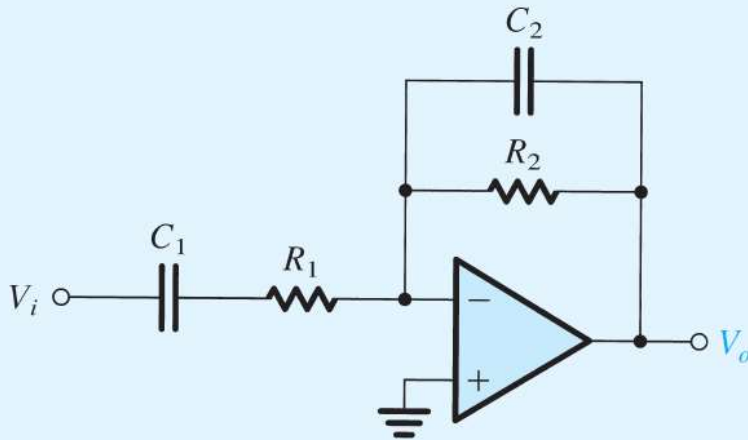
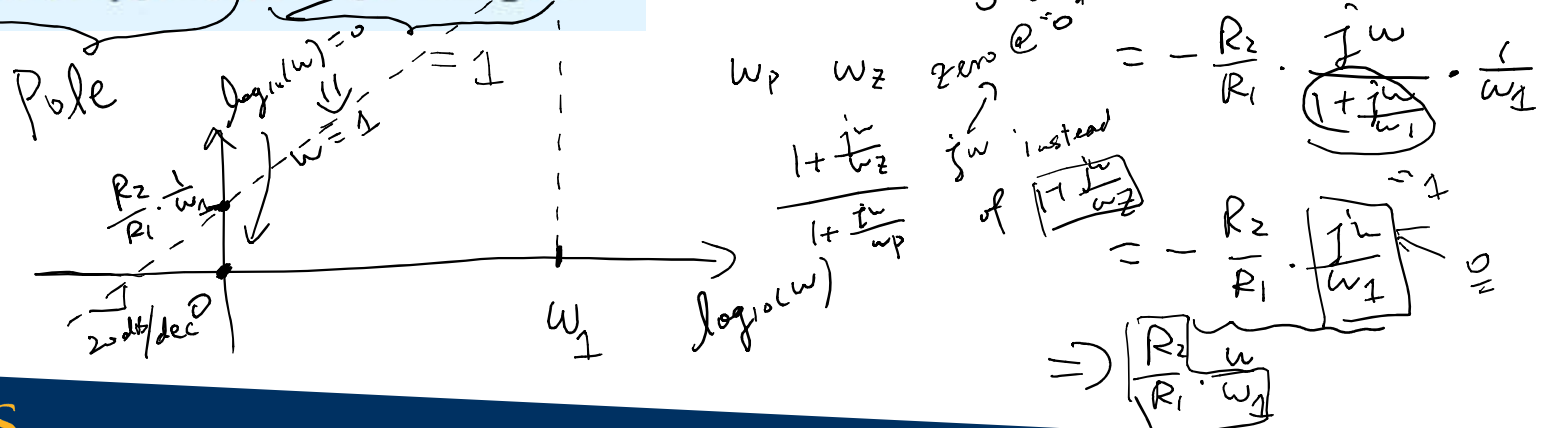


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Within a) $\omega \ll \omega_1 \ll \omega_2$

$$\frac{V_o}{V_i} = \frac{-R_2/R_1}{[1 + (\omega_1/j\omega)][1 + j(\omega/\omega_2)]}$$



S&S 2.93

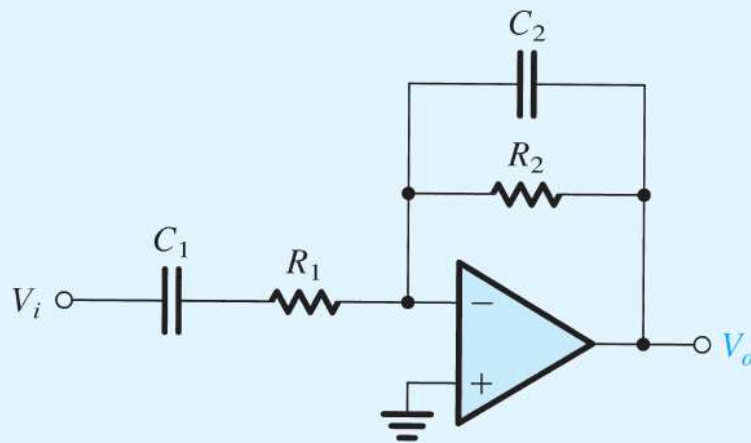
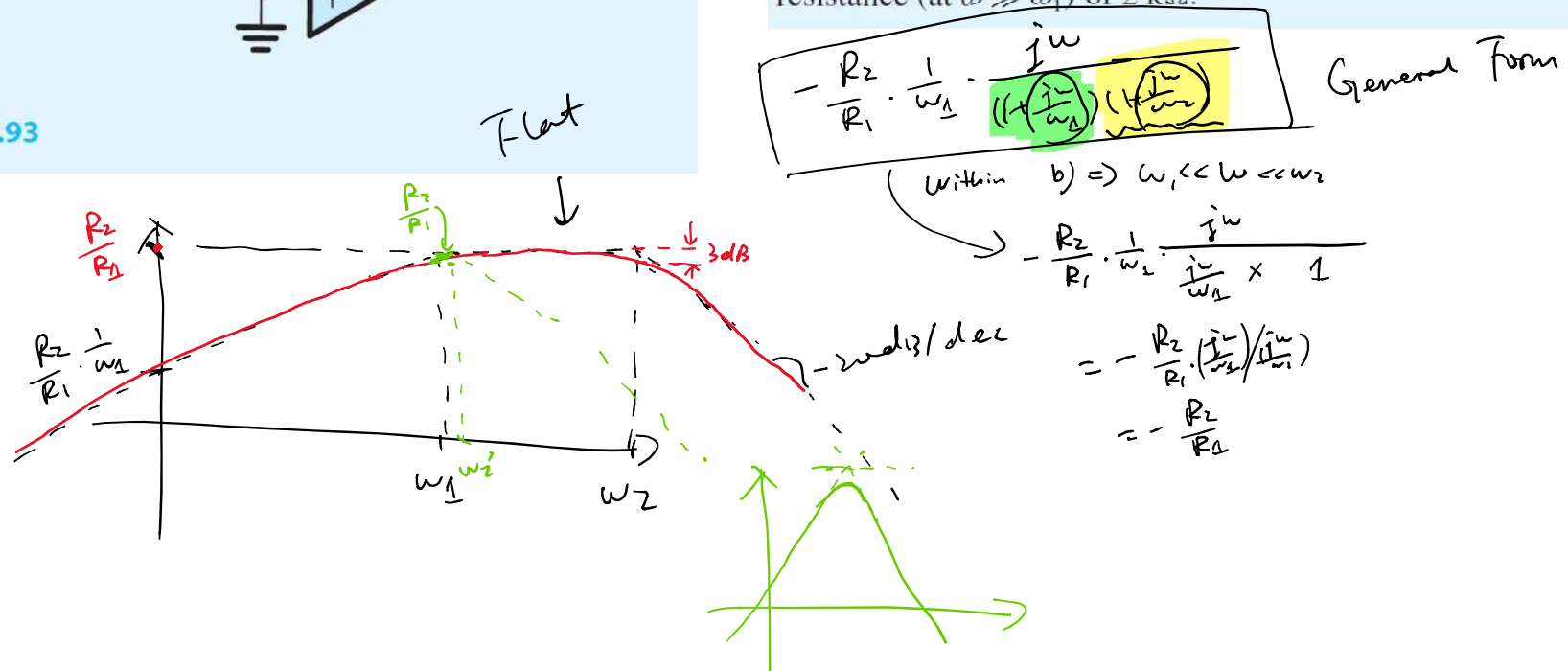


Figure P2.93

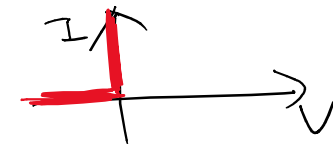
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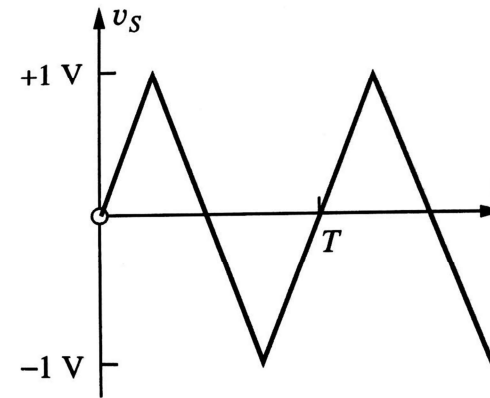
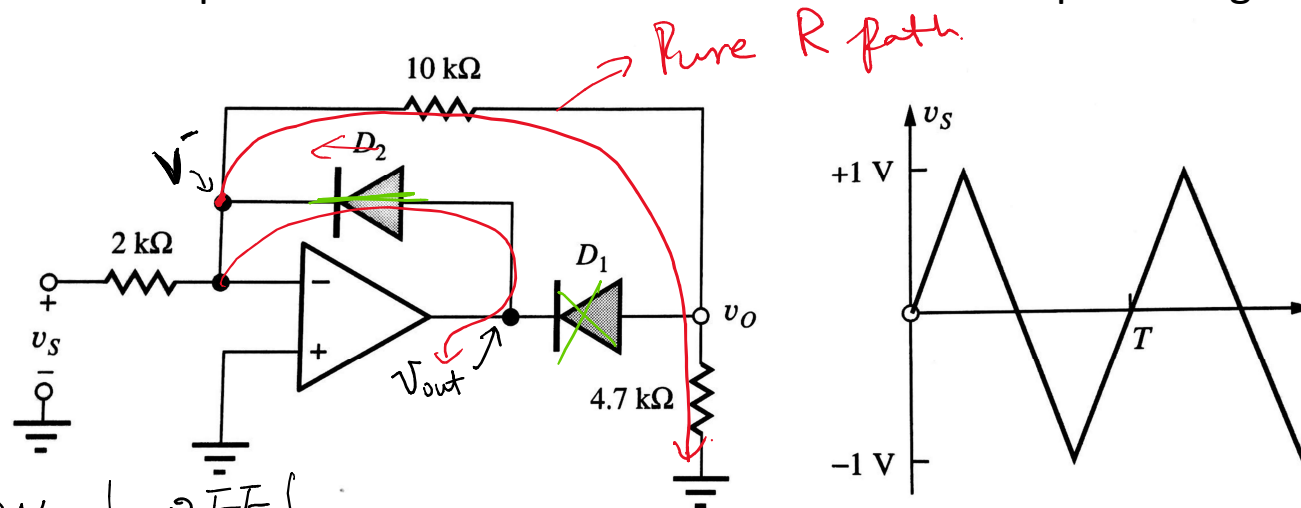
Exercise 2



Assume ideal diode model



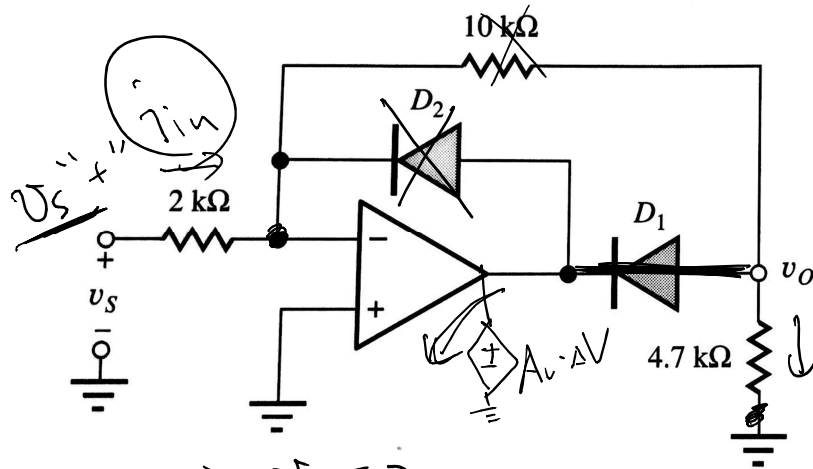
The waveform of the input voltage v_s to the circuit below is a triangle wave with a peak voltage of $1V$ and a period of T . Sketch the waveform of the output voltage v_o .



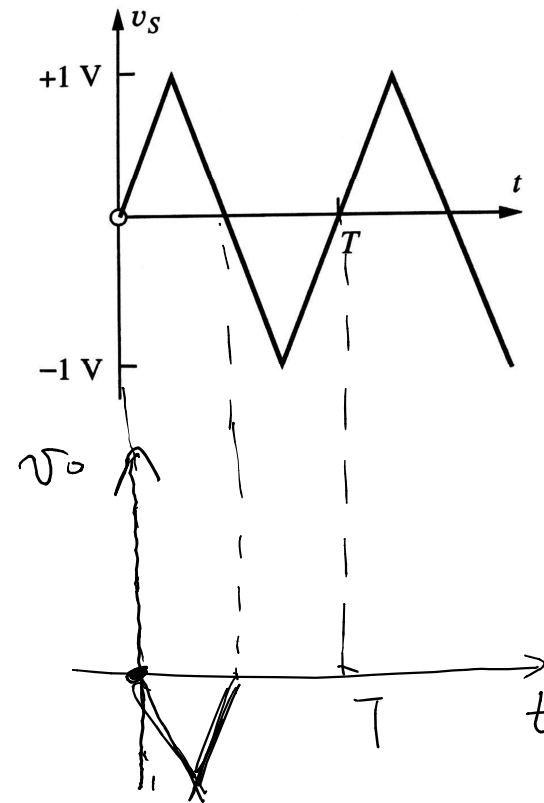
	ON	OFF
D_1	v_{out} v_o	v_{out} v_o
D_2	v_{out} v^-	v_{out} v^-

$D_1 \backslash D_2$	ON	OFF
ON		
OFF		

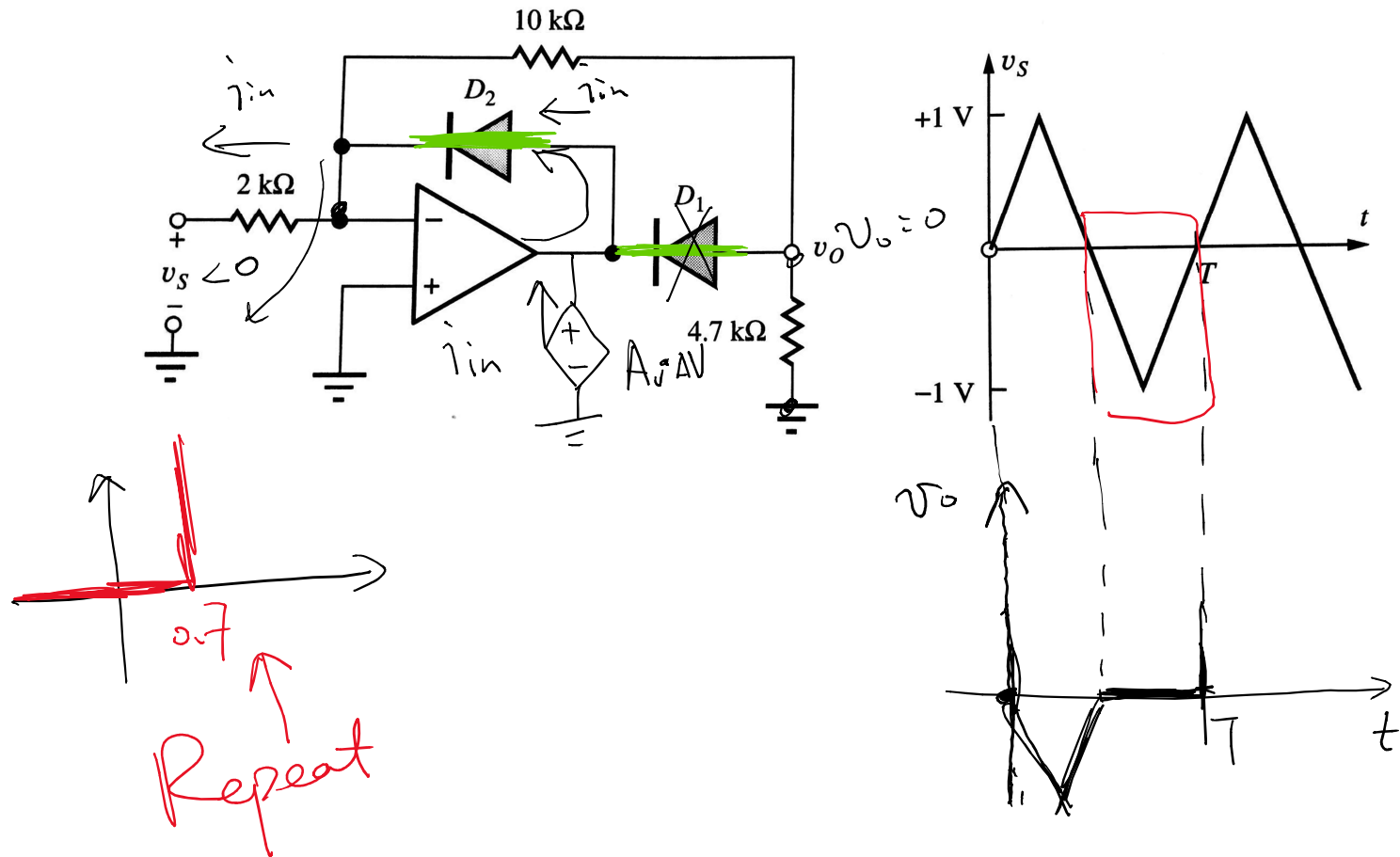
Exercise 2



$\textcircled{1} v_s = 0 \Rightarrow v_o = 0$
 $\textcircled{2} v_s > 0$



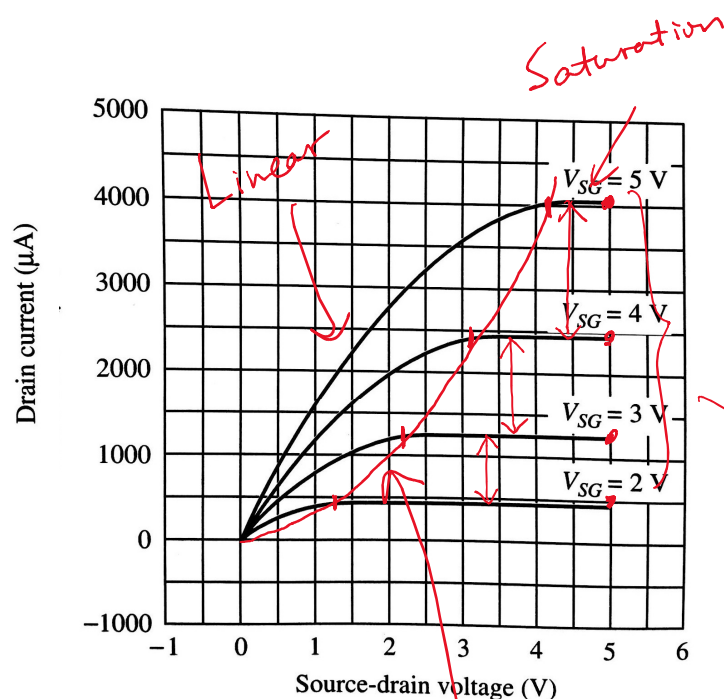
Exercise 2



Exercise 3

$$K_p = \mu_{n0} \epsilon_{ox} \frac{W}{L} \quad k'_p = \mu_{n0} \epsilon_{ox} \quad ?$$

The output characteristics for a PMOS transistor are given. What are the values of K'_p and V_{TP} for this transistor? Is this an enhancement-mode or depletion-mode transistor? What is the value of W/L if $K_p = 10 \mu A/V^2$?



Linear: $I_{SD} = \mu_p C_{ox} \frac{W}{L} \left[(V_{SG} - V_{TP}) V_{SD} - \frac{V_{SD}^2}{2} \right]$
 For $V_{SG} > 0$ & $V_{SD} \leq V_{SG} - V_{TP}$

Saturation: $I_{SD} = \frac{\mu_p C_{ox} \frac{W}{L}}{2} (V_{SG} - V_{TP})^2$
 For $V_{SG} > 0$ & $V_{SD} \geq V_{SG} - V_{TP}$

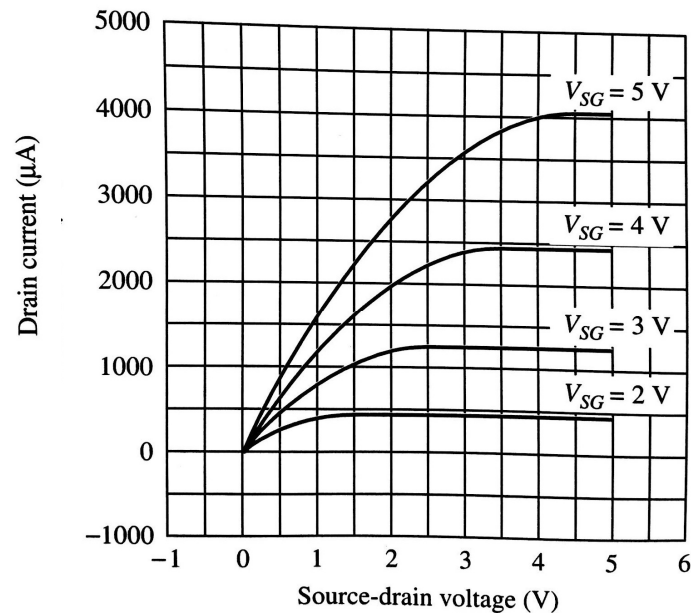
$I_1 = K_p \cdot (V_1 - V_{TP})^2$
 $I_2 = K_p \cdot (V_2 - V_{TP})^2 \Rightarrow V_{TP} \text{ & } K_p$

PMOS:	Enhancement	Depletion
	$V_T < 0$	$V_T > 0$
NMOS?	$V_T > 0$	$V_T < 0$

! $\mu_p C_{ox} \frac{W}{L} \cdot V_{SD}^2$

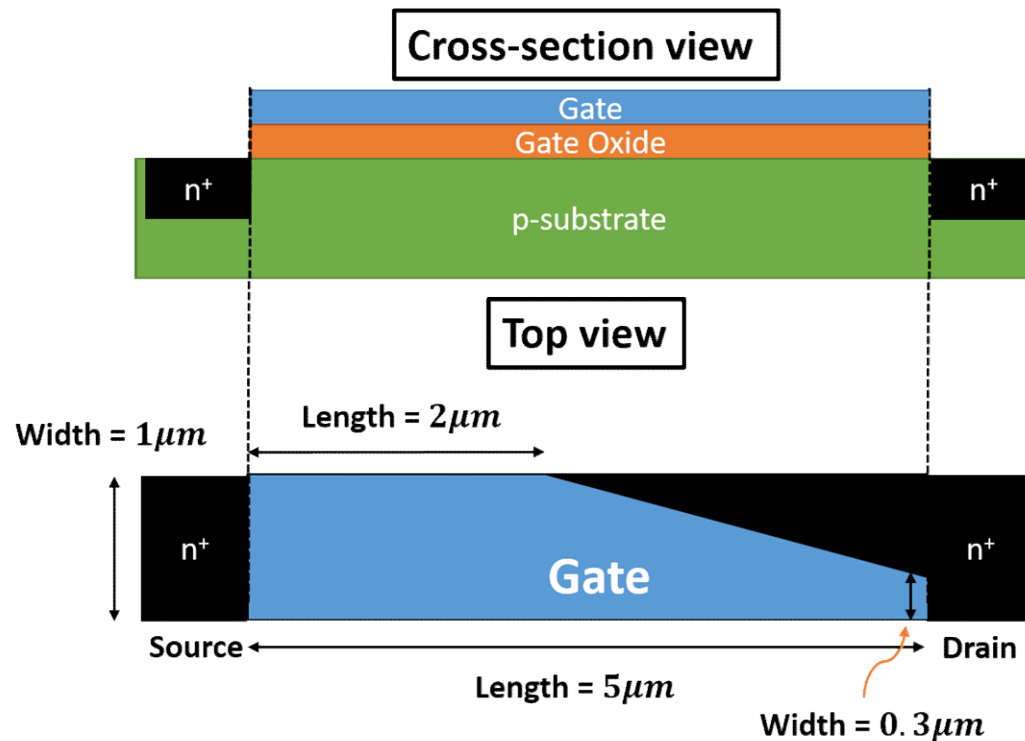
Exercise 3

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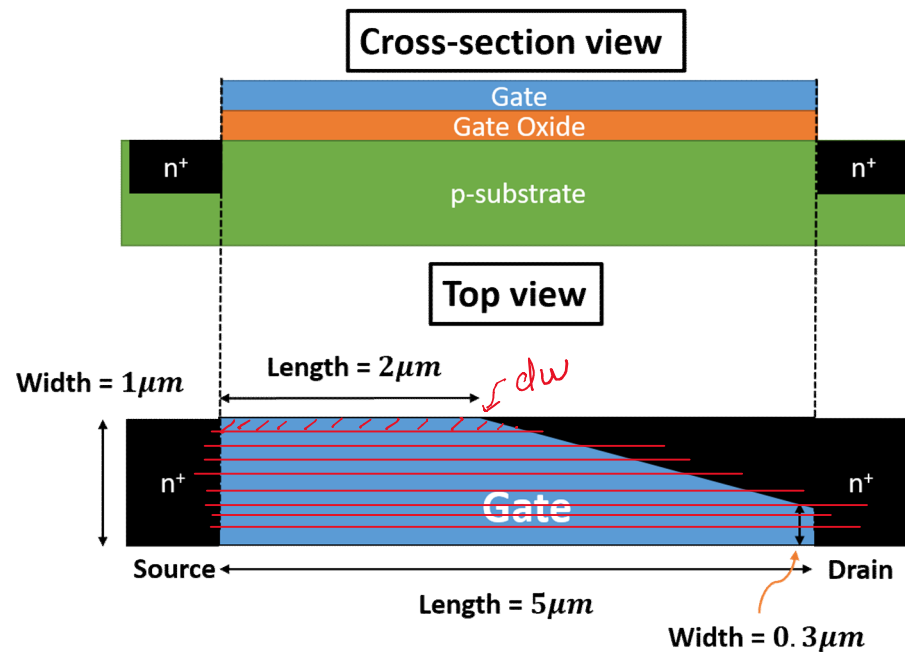


Exercise 4

Figure below presents an NMOS transistor cross-section and its top-view. Derive the expression for the device current when operating in the saturation region as a function of μ_n , C_{ox} , V_{GS} , V_{DS} and V_{th} . Assume $\lambda = 0$.



Exercise 4



$$\int_0^L I dx = \int_0^{V_{DS}} \mu_n C_{ox} \cdot \left(\frac{W}{L} \right) [V_{GS} - V_{TH} - V(x)] \cdot dV_{DS}$$

$$W = f(L)$$

$$L = f(W)$$

$$\textcircled{1} \int_0^{f(W)} \textcircled{I} dx = \int_0^{V_{DS}} \mu_n C_{ox} \frac{dw}{L} [V_{GS} - V_{TH} - V(x)] \cdot dV_{DS}$$

②

$$I_{tot} = \int_0^W I(w) dw$$

① ⇒ Solving for current within each segment w/ $W = dw$

② ⇒ Summing current within all segments w/ $W = dw$